

## SMAF Plastic-Encapsulate Diodes

High Efficient Rectifier

### Features

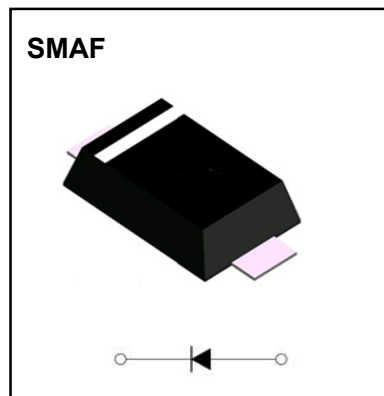
- $I_o$  1A
- $V_{RRM}$  50V-1000V
- High surge current capability
- Glass passivated chip
- Polarity: Color band denotes cathode

### Applications

- Rectifier

### Marking

- US1AF-US1MF : US1A-US1M



### Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	US							
				1AF	1BF	1DF	1FF	1GF	1JF	1KF	1MF
Repetitive Peak Reverse Voltage	$V_{RRM}$	V		50	100	200	300	400	600	800	1000
Maximum RMS Voltage	$V_{RMS}$	V		35	70	140	210	280	420	560	700
Average Forward Current	$I_{F(AV)}$	A	60Hz Half-sine wave, Resistance load, $T_L=115^\circ\text{C}$	1.0							
Surge(Non-repetitive)Forward Current	$I_{FSM}$	A	60Hz Half-sine wave, 1 cycle, $T_a=25^\circ\text{C}$	30							
Junction Temperature	$T_J$	$^\circ\text{C}$		-55 ~ +150							
Storage Temperature	$T_{STG}$	$^\circ\text{C}$		-55 ~ +150							

### Electrical Characteristics ( $T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	US							
				1AF	1BF	1DF	1FF	1GF	1JF	1KF	1MF
Peak Forward Voltage	$V_{FM}$	V	$I_{FM}=1.0\text{A}$	1.0		1.3		1.7			
Peak Reverse Current	$I_{RRM1}$	$\mu\text{A}$	$V_{RM}=V_{RRM}$	$T_a=25^\circ\text{C}$							
	$I_{RRM2}$			$T_a=125^\circ\text{C}$							
Reverse Recovery time	$t_r$	ns	$I_F=0.5\text{A}$ $I_R=1\text{A}$ $I_{RR}=0.25\text{A}$	50				75			
Thermal Resistance(Typical)	$R_{\theta J-A}$	$^\circ\text{C}/\text{W}$	Between junction and ambient	75 <sup>1)</sup>							
	$R_{\theta J-L}$		Between junction and terminal	27 <sup>1)</sup>							

### Notes:

Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

# Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

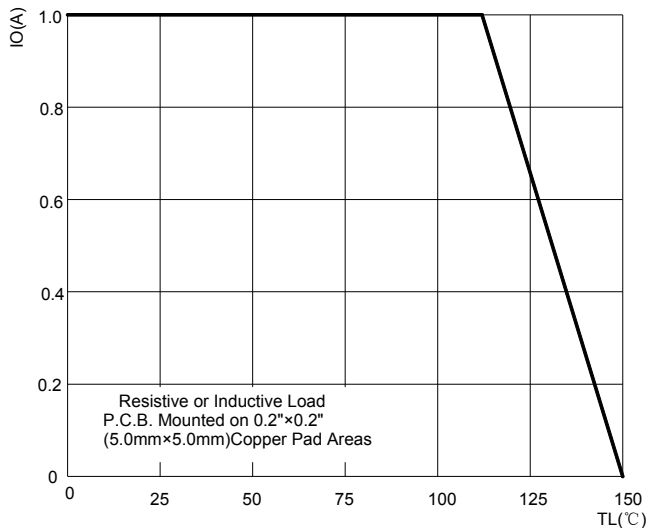


FIG.2: MAXIMUM NON-REPETITIVE FORWARD URGE CURRENT

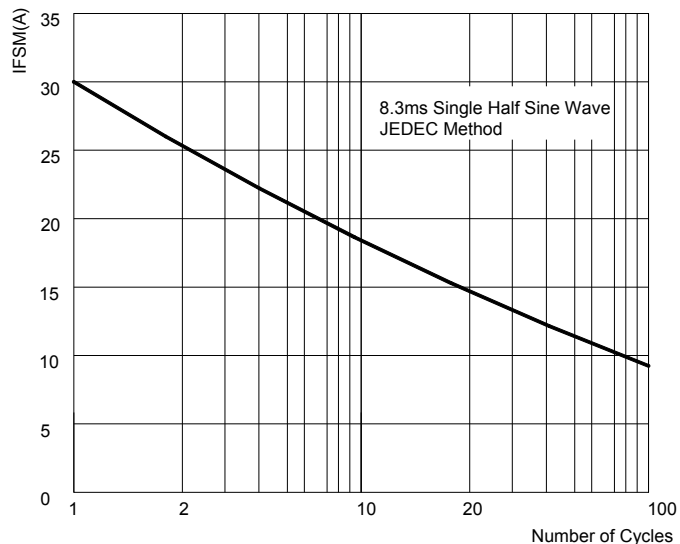


FIG.3: TYPICAL FORWARD CHARACTERISTICS

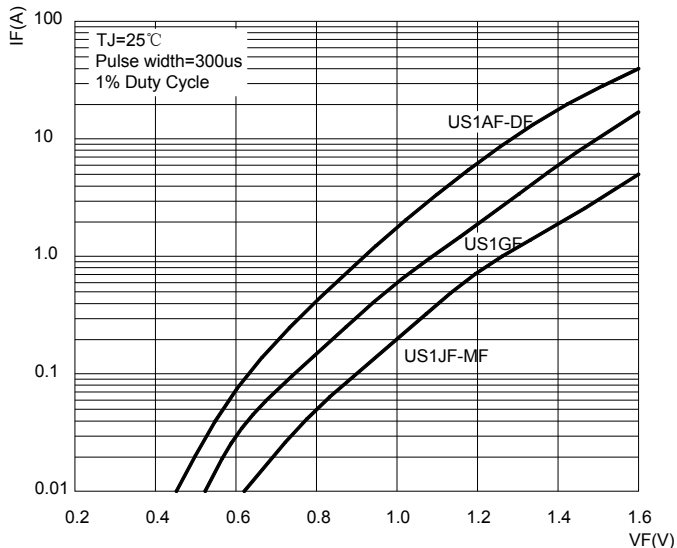


FIG.4: TYPICAL REVERSE CHARACTERISTICS

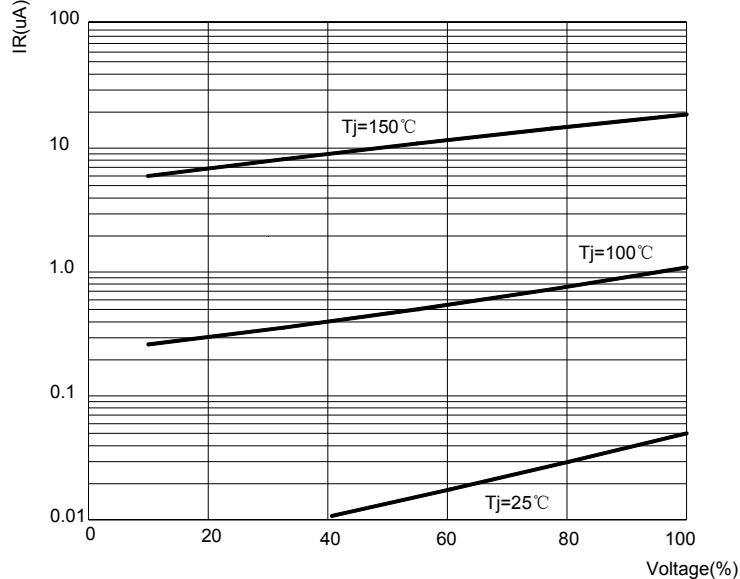
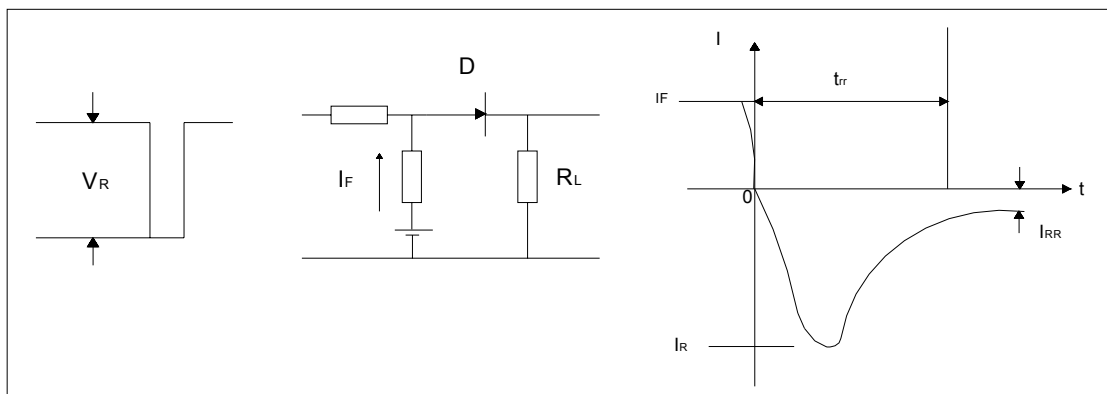
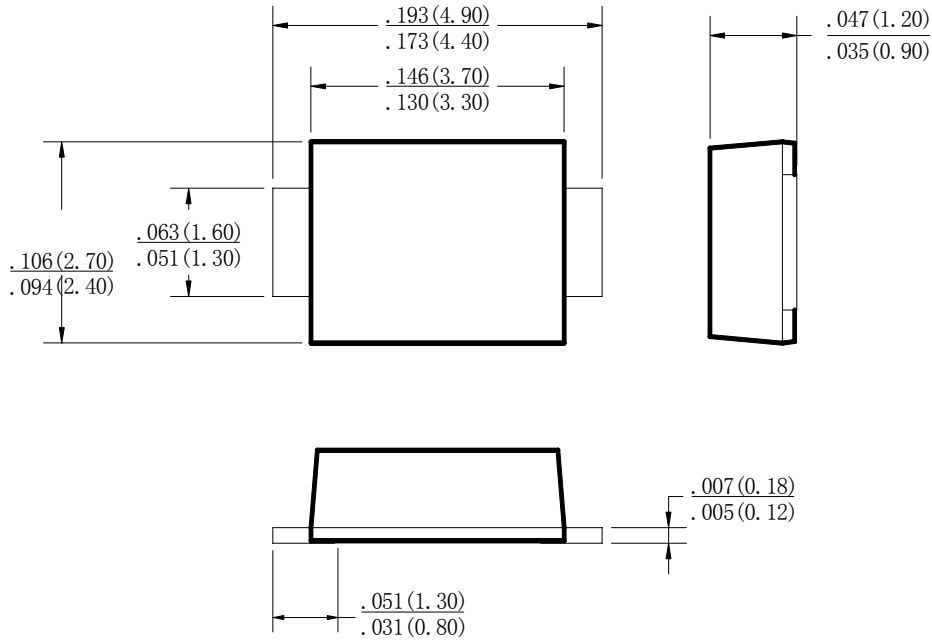


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time

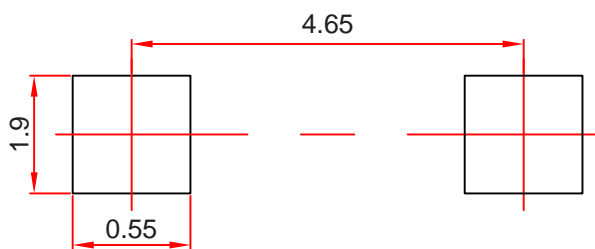


## SMAF Package Outline Dimensions



Dimensions in inches and (millimeters)

## SMAF Suggested Pad Layout

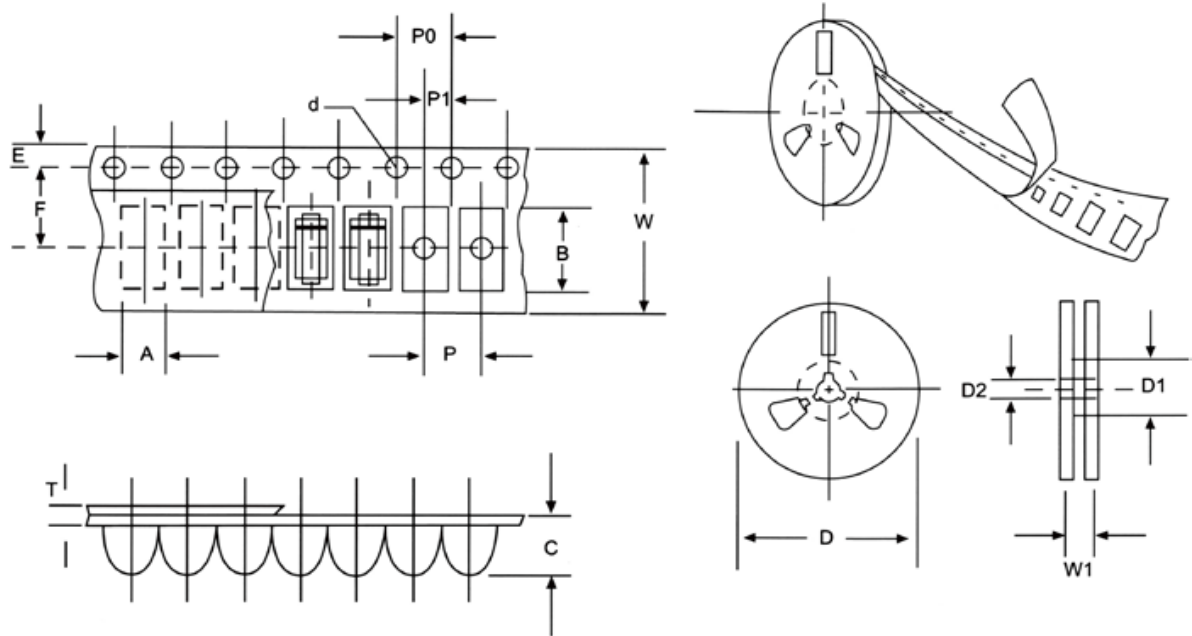


### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

### NOTICE

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**FIG:CONFIGURATION OF AXIAL TAPING**

ITEM	SYMBOL	SMAF mm(inch)
Carrier width	A	2.83+0.1(0.112+0.004)
Carrier length	B	4.90+0.1(0.193+0.004)
Carrier depth	C	1.45+0.1(0.057+0.004)
Sprocket hole	d	1.55+0.05(0.061+0.002)
Reel outside diameter	D	280/178+2.0(11/7.0+0.079)
Reel inner diameter	D1	8.0+0.2(0.315+0.008)
Feed hole diameter	D2	13+0.5(0.512+0.020)
Sprocket hole position	E	1.75+0.1(0.069+0.004)
Punch hole position	F	5.5+0.05(0.217+0.002)
Punch hole pitch	P	4.0+0.1(0.157+0.004)
Sprocket hole pitch	P0	4.0+0.1(0.157+0.004)
Embossment center	P1	2.0+0.1(0.079+0.004)
Totall tape thickness	T	0.23-0.29(0.009-0.011)
Tape width	W	12.0+0.1(0.472+0.004)
Reel width	W1	16.8+2.0(0.661+0.079)

NOTE:Devices are packde in accordance with EIA standard RS-481-A and specification given above.